Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN0606-3 (SOT8001) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 1 kV HBM
- Leadless ultra small and ultra thin SMD plastic package: 0.62 × 0.62 × 0.37 mm

3. Applications

- Relay driver
- High-speed line driver
- · High-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V _{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-	-530	mA
Static characte	ristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -500 \text{ mA}; T_j = 25 \text{ °C}$		-	1	1.4	Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D
2	S	source		
3	D	drain	Transparent top view DFN0606-3 (SOT8001)	G S 017aaa259

6. Ordering information

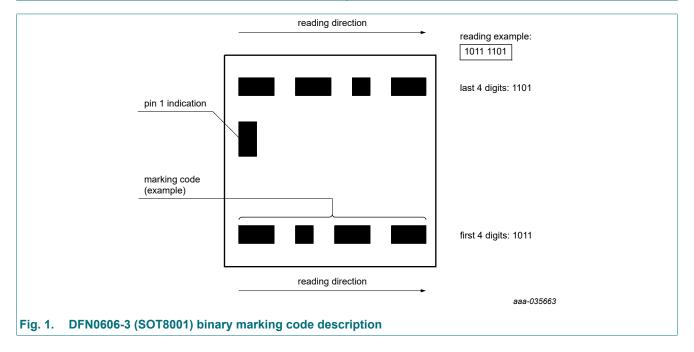
Table 3. Ordering information

· · · · · · · · · · · · · · · · · · ·						
Type number	Package					
	Name	Description	Version			
PMH950UPE	DFN0606-3	plastic, leadless ultra small package; 3 terminals; body 0.62 x 0.62 x 0.37 mm	SOT8001			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMH950UPE	0001 0100



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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions		Min	Max	Unit
drain-source voltage	T _j = 25 °C		-	-20	V
gate-source voltage			-8	8	V
drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-530	mA
	V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-360	mA
peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-2	Α
total power dissipation	T _{amb} = 25 °C	[2]	-	370	mW
		[1]	-	625	mW
	T _{sp} = 25 °C		-	2.2	W
junction temperature			-55	150	°C
ambient temperature			-55	150	°C
storage temperature			-65	150	°C
ode		•			_
source current	T _{amb} = 25 °C	[1]	-	-530	mA
	drain-source voltage gate-source voltage drain current peak drain current total power dissipation junction temperature ambient temperature storage temperature	$\begin{array}{ll} \text{drain-source voltage} & T_j = 25 \text{ °C} \\ \\ \text{gate-source voltage} \\ \\ \text{drain current} & V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C} \\ \hline V_{GS} = -4.5 \text{ V}; T_{amb} = 100 \text{ °C} \\ \\ \text{peak drain current} & T_{amb} = 25 \text{ °C}; \text{single pulse}; t_p \leq 10 \text{ µs} \\ \hline \text{total power dissipation} & T_{amb} = 25 \text{ °C} \\ \hline T_{sp} = 25 \text{ °C} \\ \hline \text{junction temperature} \\ \\ \text{ambient temperature} \\ \\ \text{storage temperature} \\ \\ \\ \text{ode} \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\$	$\begin{array}{c} \text{drain-source voltage} \\ \text{gate-source voltage} \\ \text{drain current} \\ \\ \hline \\ V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C} \\ \hline \\ V_{GS} = -4.5 \text{ V}; T_{amb} = 100 \text{ °C} \\ \hline \\ V_{GS} = -4.5 \text{ V}; T_{amb} = 100 \text{ °C} \\ \hline \\ \text{peak drain current}} \\ \hline \\ \text{total power dissipation} \\ \hline \\ T_{amb} = 25 \text{ °C}; \text{single pulse}; t_p \leq 10 \text{ µs} \\ \hline \\ \text{total power dissipation} \\ \hline \\ T_{amb} = 25 \text{ °C} \\ \hline \\ \hline \\ \text{junction temperature} \\ \hline \\ \text{ambient temperature} \\ \hline \\ \text{storage temperature} \\ \hline \\ \textbf{ode} \\ \hline \\ \hline \end{array}$	$\begin{array}{c} \text{drain-source voltage} \\ \text{gate-source voltage} \\ \text{drain current} \\ \\ \hline \\ V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C} \\ \hline \\ V_{GS} = -4.5 \text{ V}; T_{amb} = 100 \text{ °C} \\ \hline \\ V_{GS} = -4.5 \text{ V}; T_{amb} = 100 \text{ °C} \\ \hline \\ \text{peak drain current}} \\ \hline \\ \text{total power dissipation} \\ \hline \\ T_{amb} = 25 \text{ °C}; \text{single pulse}; t_p \leq 10 \text{ µs} \\ \hline \\ \text{total power dissipation} \\ \hline \\ T_{amb} = 25 \text{ °C} \\ \hline \\ \text{[1]} \\ \hline \\ T_{sp} = 25 \text{ °C} \\ \hline \\ \text{junction temperature} \\ \hline \\ \text{ambient temperature} \\ \hline \\ \text{storage temperature} \\ \hline \\ \text{ode} \\ \hline \\ \end{array}$	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

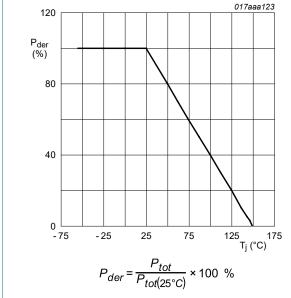


Fig. 2. Normalized total power dissipation as a function of junction temperature

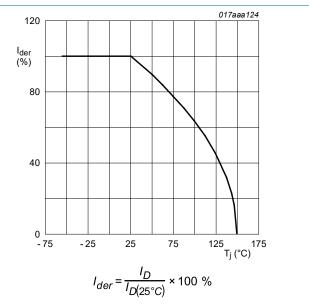


Fig. 3. Normalized continuous drain current as a function of junction temperature

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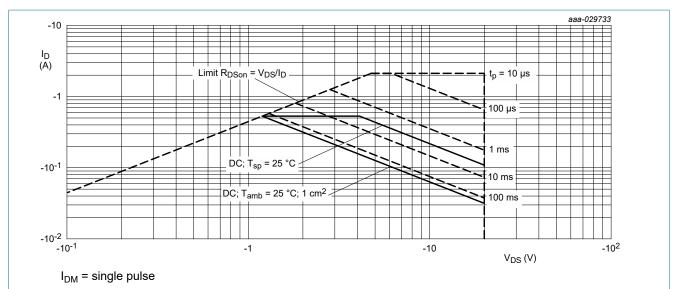


Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

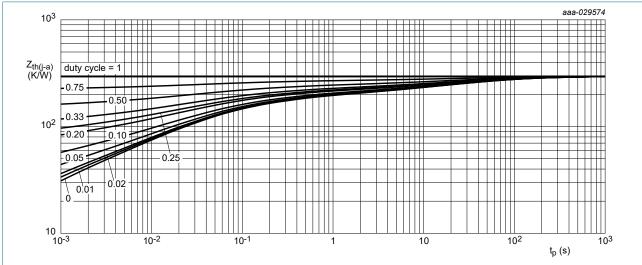
20 V, P-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

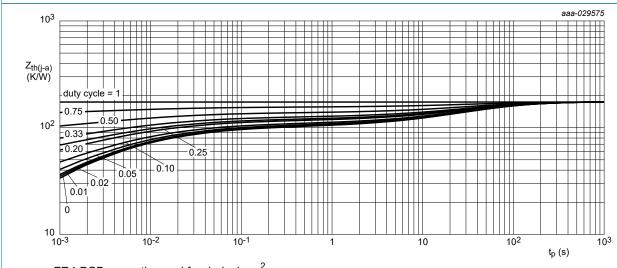
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	300	340	K/W
junction to ambient		[2]	-	175	200	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	50	58	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².



FR4 PCB, standard footprint

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I_D = -250 μ A; V_{GS} = 0 V; T_j = 25 °C	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.45	-0.7	-0.95	V
I _{DSS}	drain leakage current	V _{DS} = -20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μA
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
		$V_{GS} = 2.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
		V _{GS} = -2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon} drain-source on-state resistance	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -500 \text{ mA}; T_j = 25 ^{\circ}\text{C}$	-	1	1.4	Ω
	resistance	V _{GS} = -4.5 V; I _D = -500 mA; T _j = 150 °C	-	1.6	2.3	Ω
		V_{GS} = -2.5 V; I_D = -200 mA; T_j = 25 °C	-	1.4	2.2	Ω
		V_{GS} = -1.8 V; I_D = -40 mA; T_j = 25 °C	-	1.8	3.3	Ω
		V_{GS} = -1.5 V; I_D = -40 mA; T_j = 25 °C	-	2.1	5.5	Ω
		V_{GS} = -1.2 V; I_D = -10 mA; T_j = 25 °C	-	2.9	-	Ω
g _{fs}	forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -600 \text{ mA}; T_j = 25 \text{ °C}$	-	700	-	mS
R _G	gate resistance	f = 1 MHz	-	3.7	-	Ω
Dynamic cl	haracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -600 mA; V_{GS} = -4 V;	-	0.29	0.5	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.08	-	nC
Q _{GD}	gate-drain charge		-	0.08	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	36	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	6.3	-	pF
C _{rss}	reverse transfer capacitance		-	4.7	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -600 mA; V_{GS} = -4 V;	-	1	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	2	-	ns
t _{d(off)}	turn-off delay time	1	-	4	-	ns
t _f	fall time	1 –	-	6	-	ns
Source-dra	nin diode		1	1		1
V _{SD}	source-drain voltage	I _S = -600 mA; V _{GS} = 0 V; T _i = 25 °C	-	-0.7	-1.2	V

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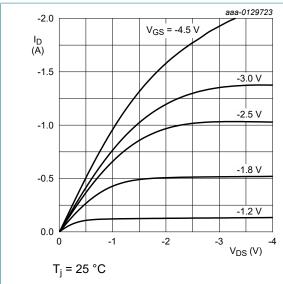


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values Fig. 8.

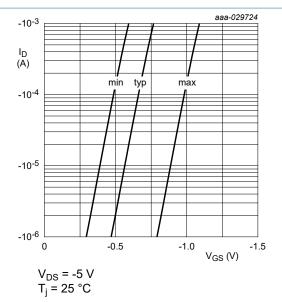


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

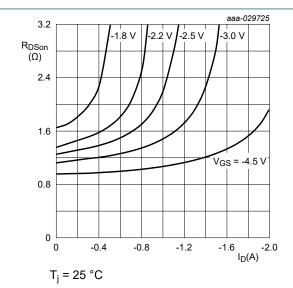


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

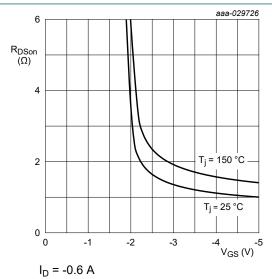


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

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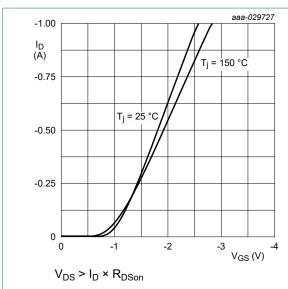


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

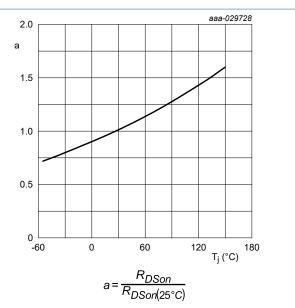


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

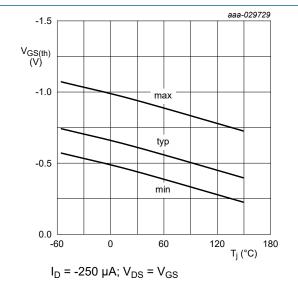


Fig. 13. Gate-source threshold voltage as a function of junction temperature

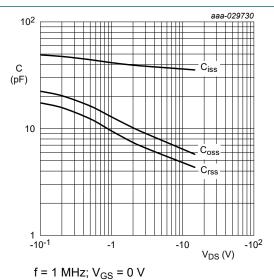


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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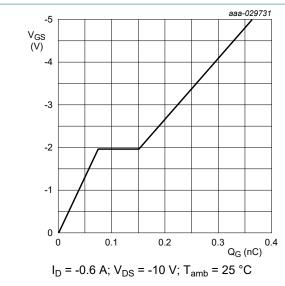


Fig. 15. Gate-source voltage as a function of gate charge; typical values

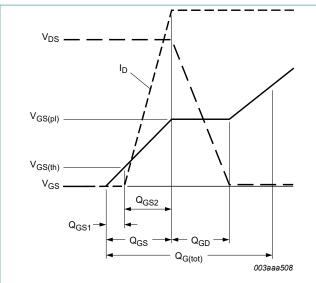


Fig. 16. Gate charge waveform definitions

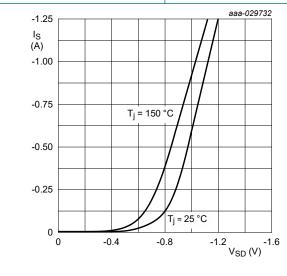
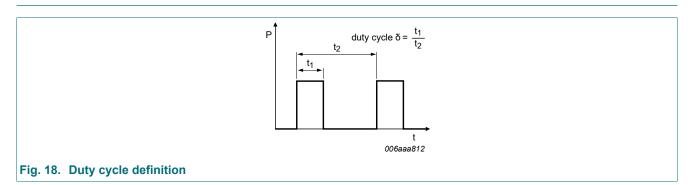


Fig. 17. Source current as a function of source-drain voltage; typical values

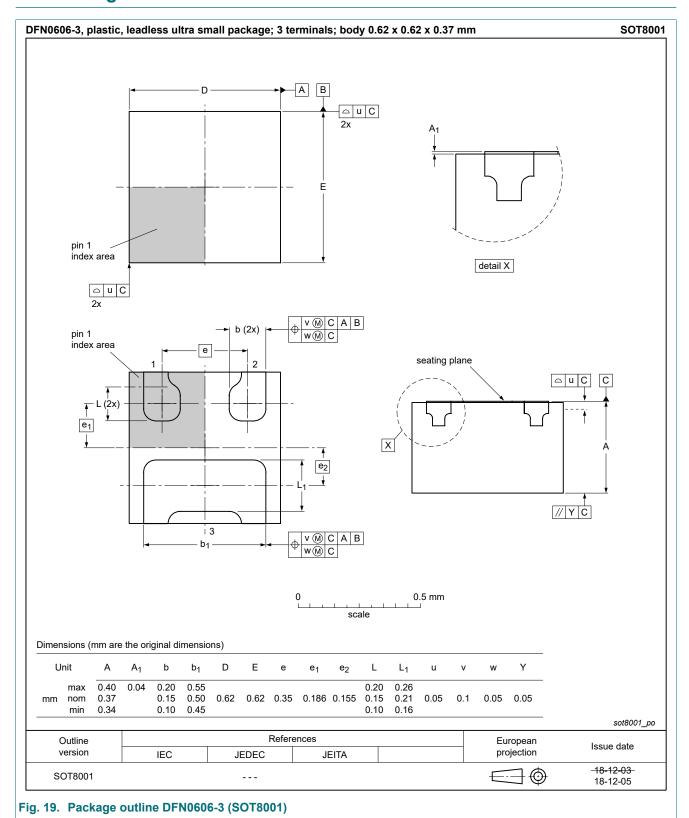
11. Test information

 $V_{GS} = 0 V$



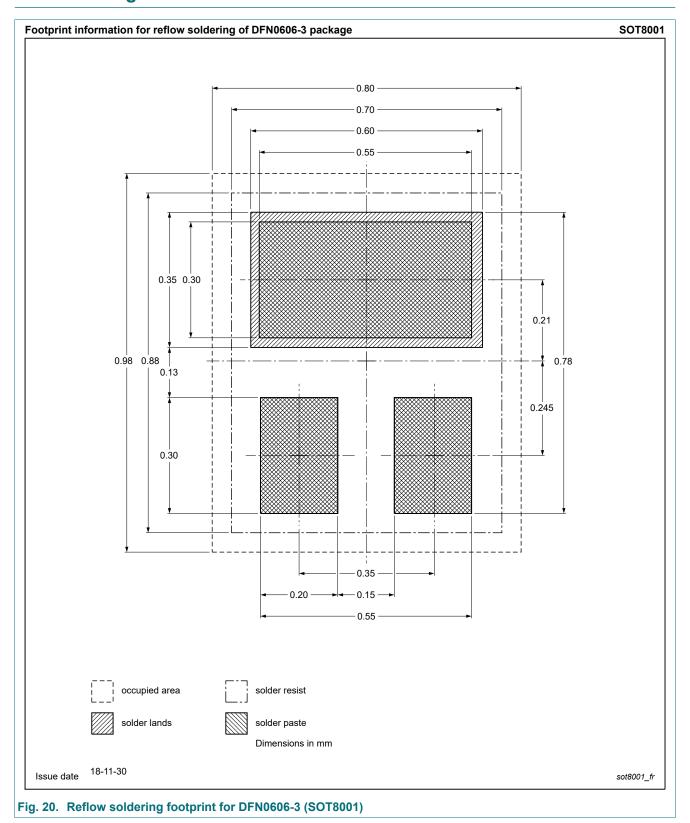
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PMH950UPE v.2	20230206	Product data sheet	-	PMH950UPE v.1				
Modifications:	Fig. 1, clarifying the	Fig. 1, clarifying the reading example						
PMH950UPE v.1	20190405	Product data sheet	-	-				

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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